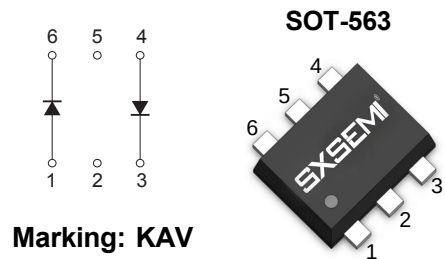


FEATURES

Surface mount schottky barrier diode arrays



Maximum Ratings @Ta=25°C

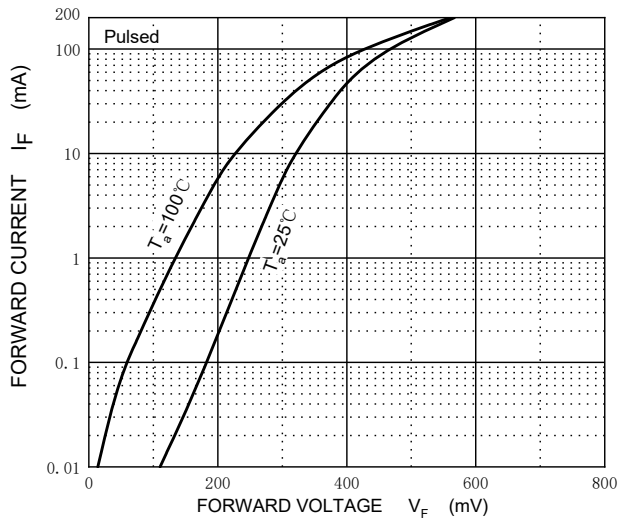
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
Average Rectified Output Current	I_O	200	mA
Non-repetitive Peak Forward Surge Current @ $t=8.3ms$	I_{FSM}	600	mA
Repetitive Peak Forward Current @ $t \leq 1s, \delta \leq 0.5$	I_{FRM}	300	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	667	°C/W
Operating Junction Temperature Range	T_J	-40 ~ +125	°C
Storage Temperature Range	T_{STG}	-55 ~ +125	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

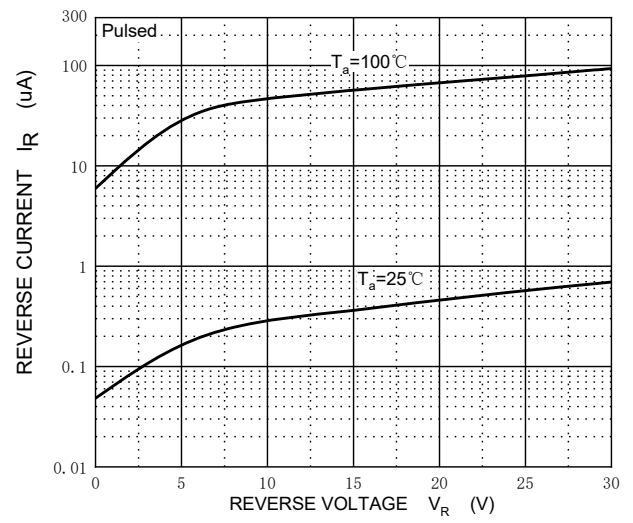
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	30		V
Reverse voltage leakage current	I_R	$V_R = 25V$		2	μA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$		320 400 500 1000	mV
Total capacitance	C_T	$V_R = 1V, f = 1MHz$		10	pF
Reverse recovery time	t_{rr}	$I_F = 10mA, I_R = 10mA \sim 1mA$ $R_L = 100\Omega$		5	ns

Typical Characteristics

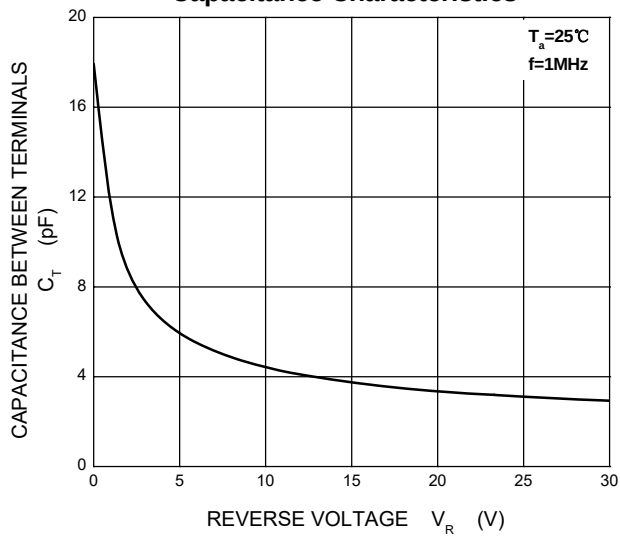
Forward Characteristics



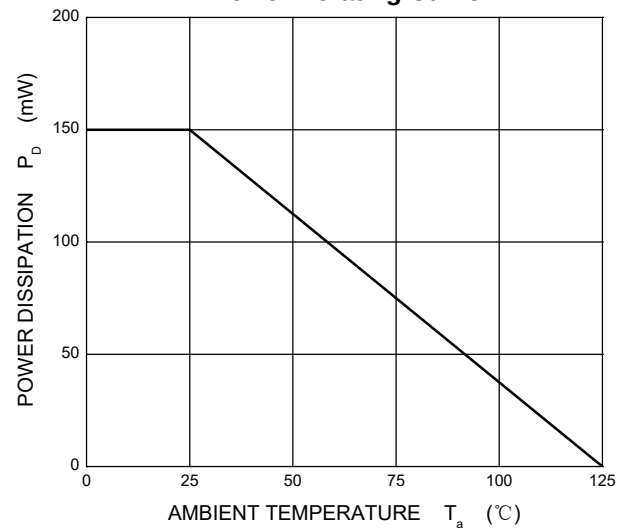
Reverse Characteristics



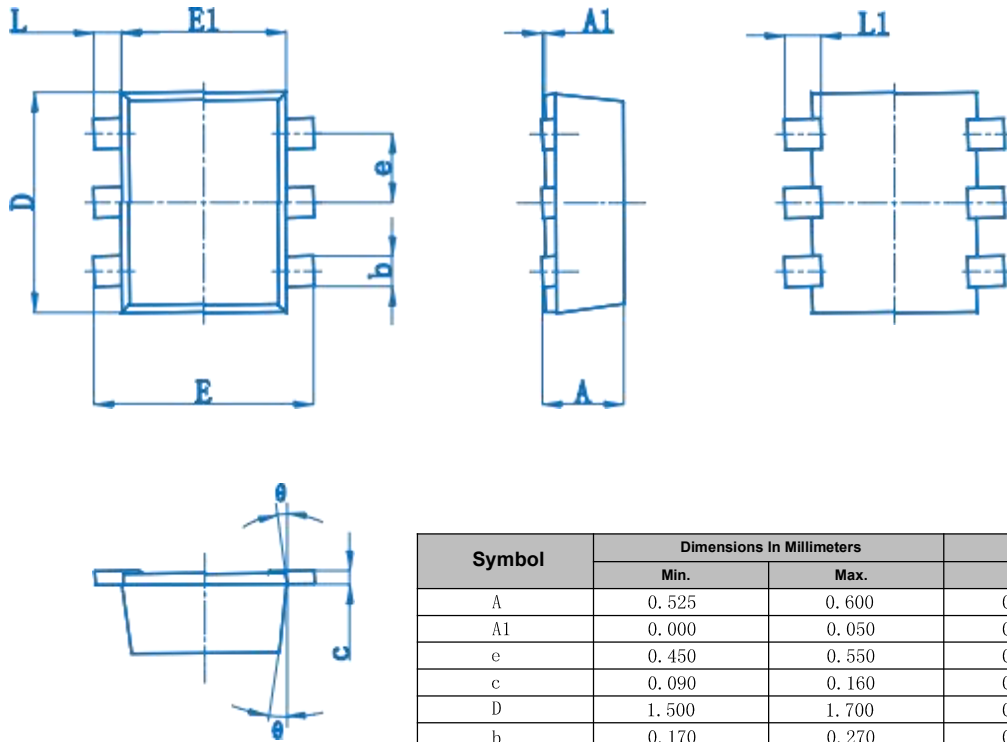
Capacitance Characteristics



Power Derating Curve

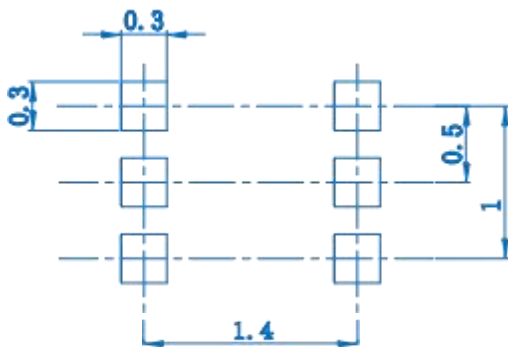


SOT-563 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.525	0.600	0.021	0.024
A1	0.000	0.050	0.000	0.002
e	0.450	0.550	0.018	0.022
c	0.090	0.160	0.004	0.006
D	1.500	1.700	0.059	0.067
b	0.170	0.270	0.007	0.011
E1	1.100	1.300	0.043	0.051
E	1.500	1.700	0.059	0.067
L	0.100	0.300	0.004	0.012
L1	0.200	0.400	0.008	0.016
θ	10° REF.		10° REF.	

SOT-563 Suggested Pad Layout



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.05 mm.
 3. The pad layout is for reference purposes only.